



Final data

SPW47N60C3

Cool MOS™ Power Transistor

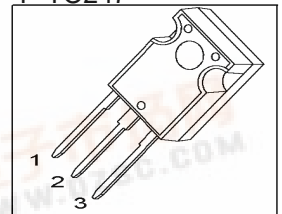
Feature

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances

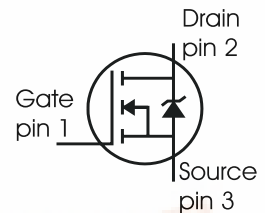
Product Summary

$V_{DS} @ T_{jmax}$	650	V
$R_{DS(on)}$	0.07	Ω
I_D	47	A

P-TO247



Type	Package	Ordering Code	Marking
SPW47N60C3	P-TO247	Q67040-S4491	47N60C3



Maximum Ratings, at $T_C = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	I_D	47	A
$T_C = 25^\circ\text{C}$		47	
$T_C = 100^\circ\text{C}$		30	
Pulsed drain current, t_p limited by T_{jmax}	$I_{D\text{ puls}}$	141	
Avalanche energy, single pulse	E_{AS}	1800	mJ
$I_D=10\text{A}, V_{DD}=50\text{V}$			
Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹⁾	E_{AR}	1	
$I_D=20\text{A}, V_{DD}=50\text{V}$			
Avalanche current, repetitive t_{AR} limited by T_{jmax}	I_{AR}	20	A
Reverse diode dv/dt	dv/dt	6	V/ns
$I_S=47\text{A}, V_{DS} < V_{DD}, di/dt=100\text{A}/\mu\text{s}, T_{jmax}=150^\circ\text{C}$			
Gate source voltage static	V_{GS}	± 20	V
Gate source voltage AC ($f > 1\text{Hz}$)	V_{GS}	± 30	
Power dissipation, $T_C = 25^\circ\text{C}$	P_{tot}	415	W
Operating and storage temperature	T_j, T_{stg}	-55... +150	$^\circ\text{C}$



Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Thermal resistance, junction - case	R_{thJC}	-	-	0.3	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}	-	-	62	
Linear derating factor		-	-	3.33	W/K
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	T_{sold}	-	-	260	°C

Electrical Characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Static Characteristics

Drain-source breakdown voltage $V_{GS}=0V, I_D=0.25mA$	$V_{(BR)DSS}$	600	-	-	V
Drain-source avalanche breakdown voltage $V_{GS}=0V, I_D=20A$	$V_{(BR)DS}$	-	700	-	
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=2.7mA$	$V_{GS(th)}$	2.1	3	3.9	
Zero gate voltage drain current $V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}, T_j = 25\text{ °C}$ $V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}, T_j = 150\text{ °C}$	I_{DSS}	-	0.5	25	μA
		-	-	250	
Gate-source leakage current $V_{GS}=30V, V_{DS}=0V$	I_{GSS}	-	-	100	nA
Drain-source on-state resistance $V_{GS}=10V, I_D=47A, T_j=25\text{ °C}$	$R_{DS(on)}$	-	0.06	0.07	Ω
Gate input resistance $f = 1\text{ MHz}, \text{open drain}$	R_G	-	0.62	-	

¹ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} * f$.

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Characteristics						
Transconductance	g_{fs}	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ $I_D = 30\text{A}$	-	40	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$	-	6800	-	pF
Output capacitance	C_{oss}		-	2200	-	
Reverse transfer capacitance	C_{rss}		-	145	-	
Effective output capacitance, 1) energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 480\text{V}$	-	193	-	pF
Effective output capacitance, 2) time related	$C_{o(tr)}$		-	412	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 380\text{V}$, $V_{GS} = 0/13\text{V}$, $I_D = 47\text{A}$, $R_G = 1.8\Omega$, $T_j = 125$	-	18	-	ns
Rise time	t_r		-	27	-	
Turn-off delay time	$t_{d(off)}$		-	111	165	
Fall time	t_f		-	8	12	

Gate Charge Characteristics

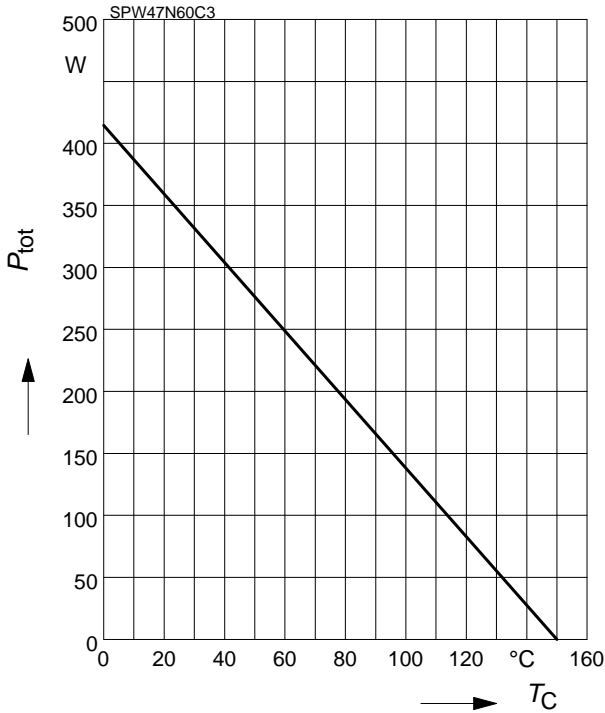
Gate to source charge	Q_{gs}	$V_{DD} = 350\text{V}$, $I_D = 47\text{A}$	-	24	-	nC
Gate to drain charge	Q_{gd}		-	121	-	
Gate charge total	Q_g	$V_{DD} = 350\text{V}$, $I_D = 47\text{A}$, $V_{GS} = 0\text{ to } 10\text{V}$	-	252	320	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350\text{V}$, $I_D = 47\text{A}$	-	5.5	-	V

¹ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

² $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

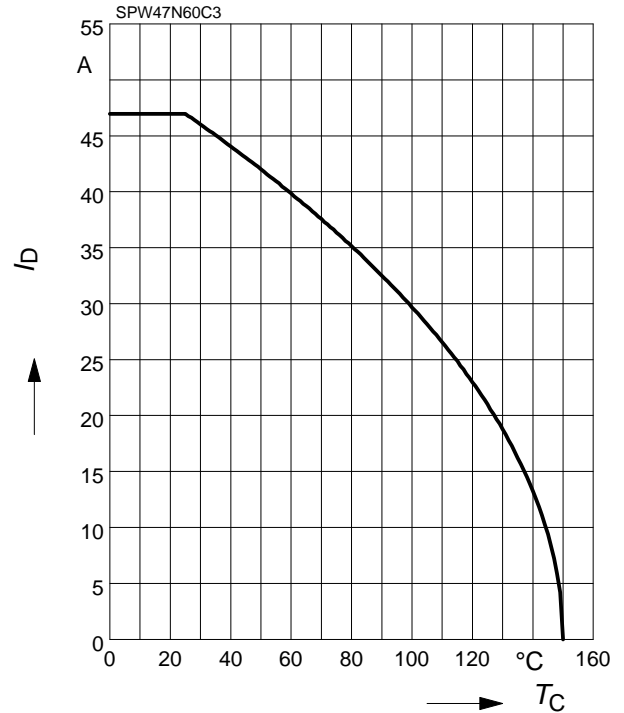
$$P_{tot} = f(T_C)$$



2 Drain current

$$I_D = f(T_C)$$

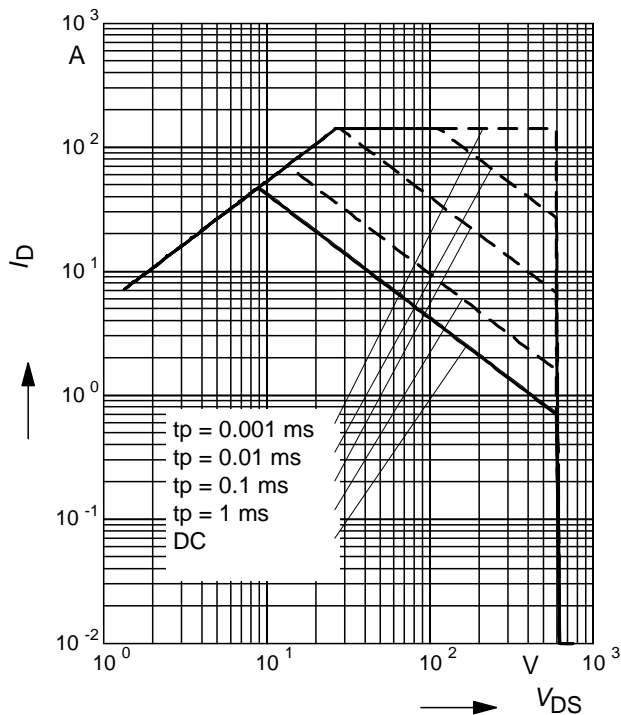
parameter: $V_{GS} \geq 10 \text{ V}$



3 Safe operating area

$$I_D = f(V_{DS})$$

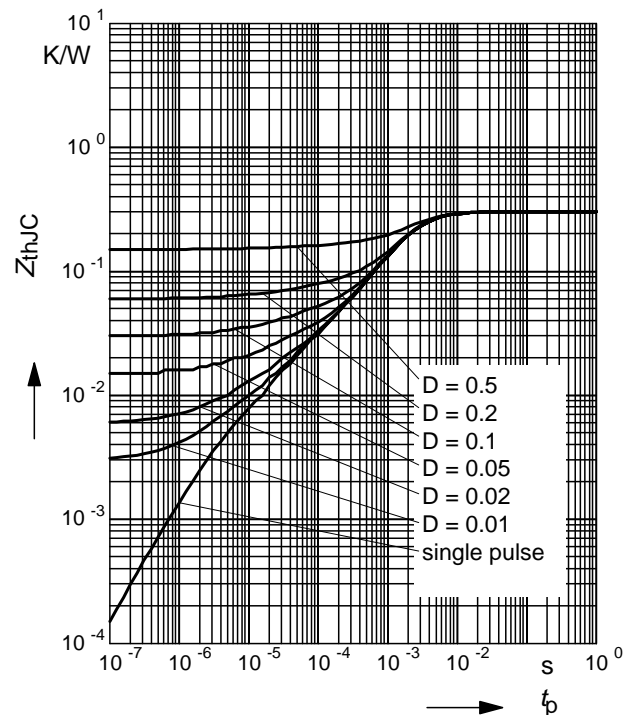
parameter: $D = 0, T_C = 25^\circ\text{C}$



4 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

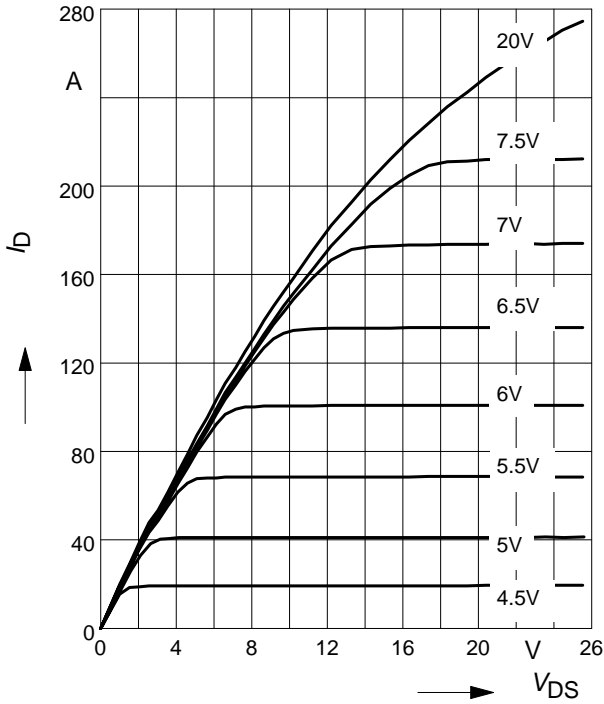
parameter: $D = t_p/T$



5 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

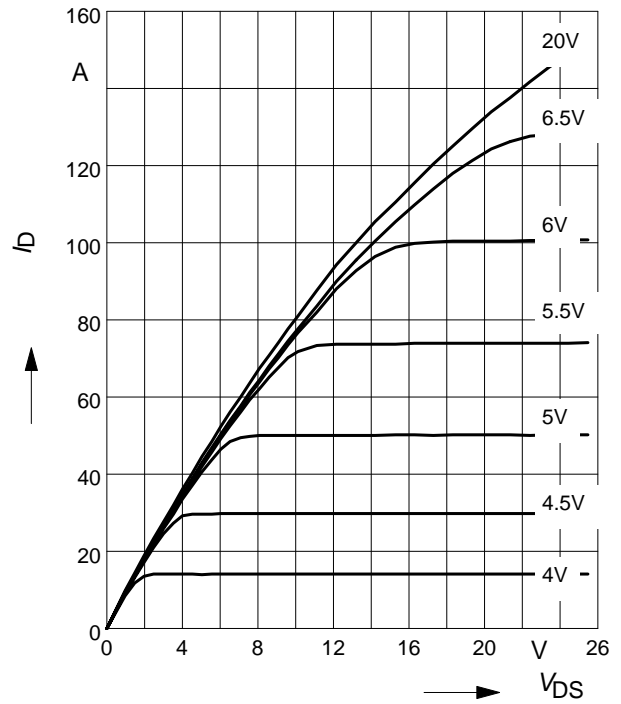
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



6 Typ. output characteristic

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

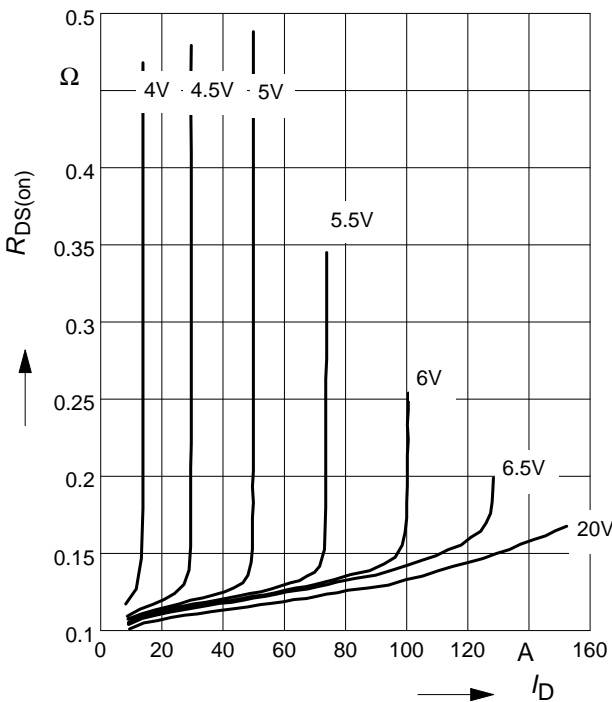
parameter: $t_p = 10 \mu\text{s}, V_{GS}$



7 Typ. drain-source on resistance

$R_{DS(on)} = f(I_D)$

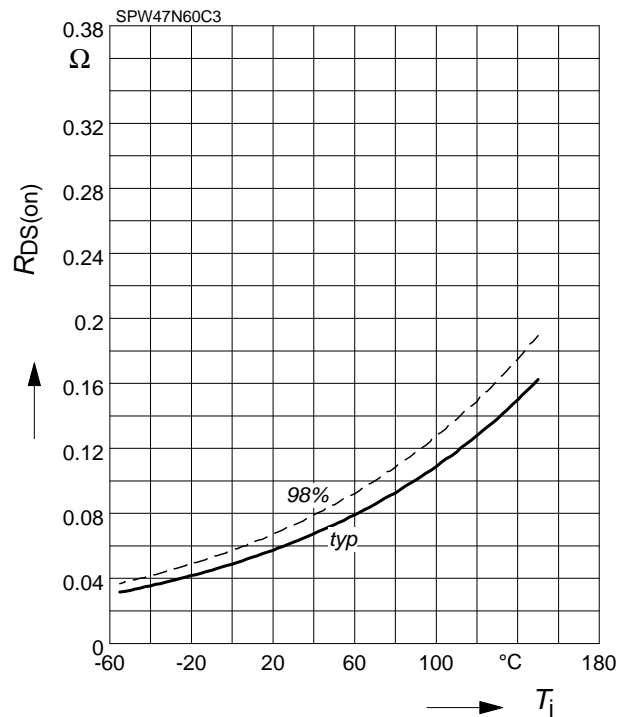
parameter: $T_j = 150^\circ\text{C}, V_{GS}$



8 Drain-source on-state resistance

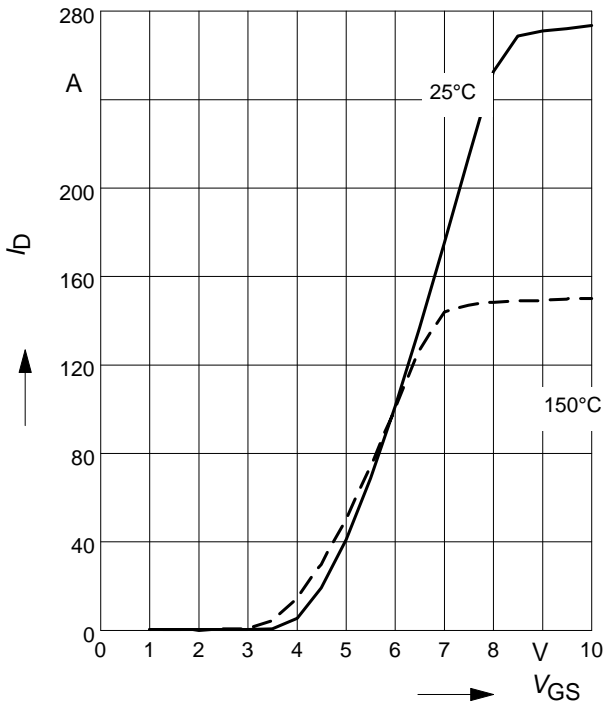
$R_{DS(on)} = f(T_j)$

parameter: $I_D = 47 \text{ A}, V_{GS} = 10 \text{ V}$



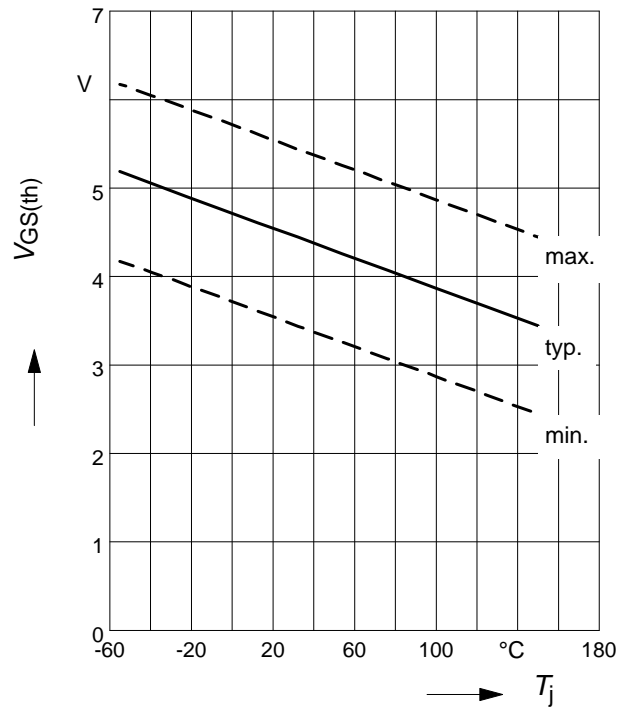
9 Typ. transfer characteristics

$I_D = f(V_{GS})$; $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$
 parameter: $t_p = 10 \mu s$



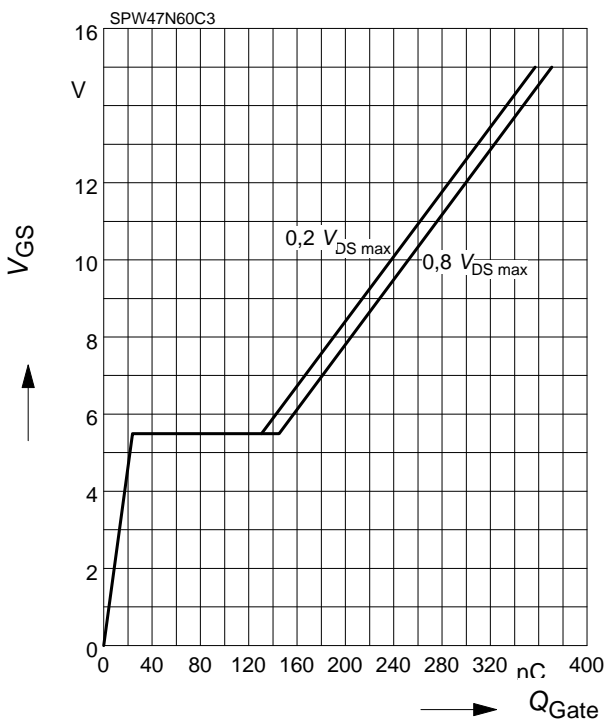
10 Gate threshold voltage

$V_{GS(th)} = f(T_j)$
 parameter: $V_{GS} = V_{DS}$, $I_D = 2.7mA$



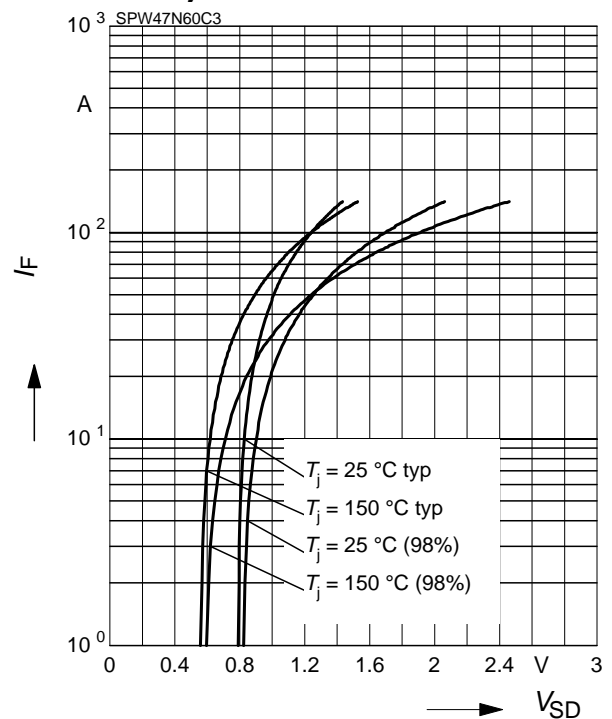
11 Typ. gate charge

$V_{GS} = f(Q_{Gate})$
 parameter: $I_D = 47 A$ pulsed



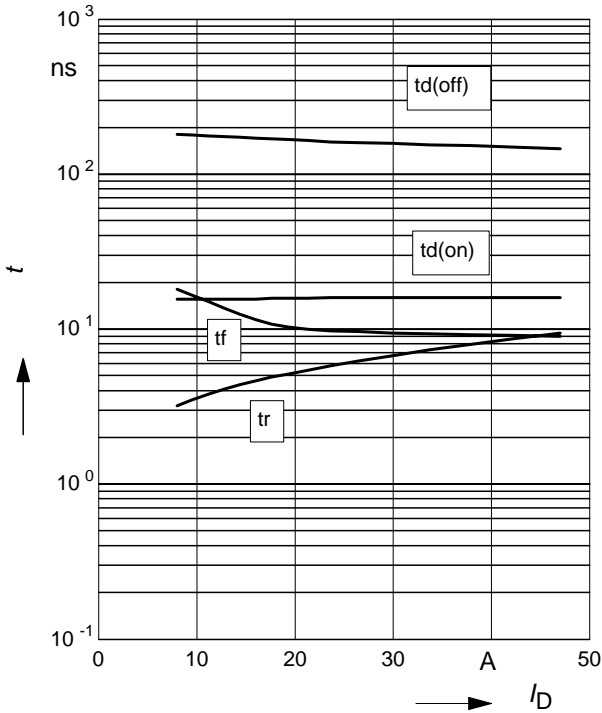
12 Forward characteristics of body diode

$I_F = f(V_{SD})$
 parameter: T_j , $t_p = 10 \mu s$



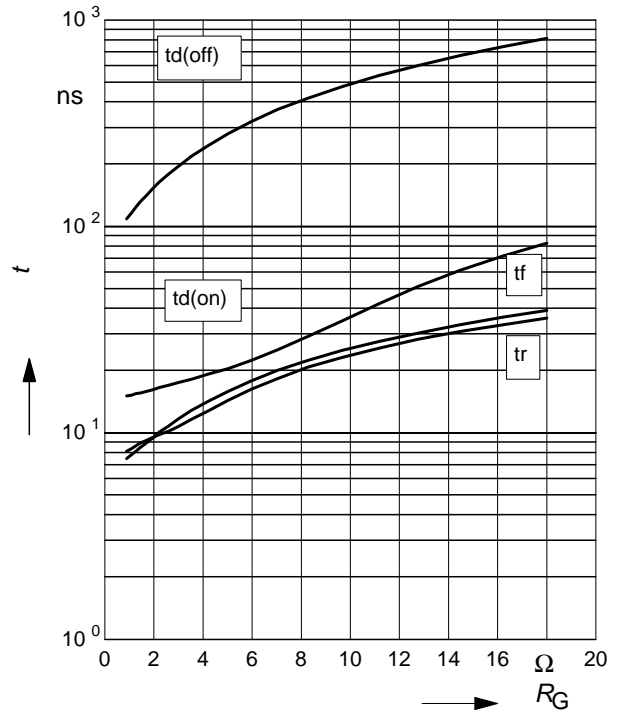
13 Typ. switching time

$t = f(I_D)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $R_G = 1.8\Omega$



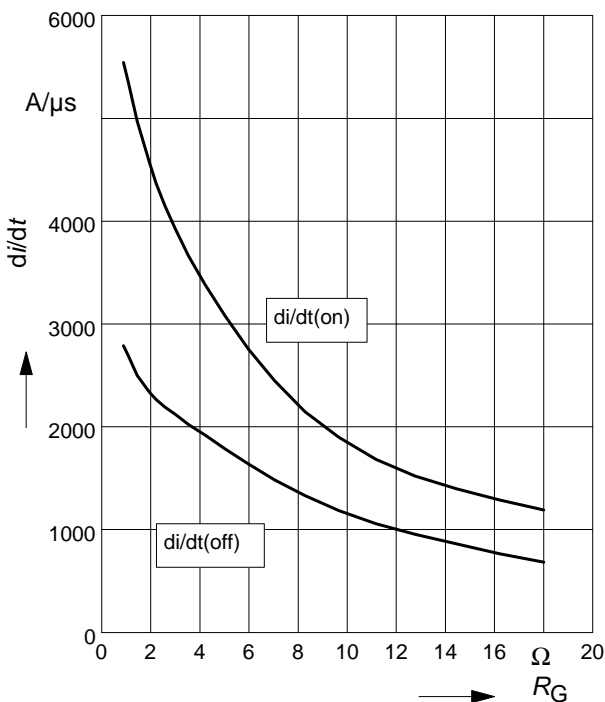
14 Typ. switching time

$t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $I_D = 47\text{A}$



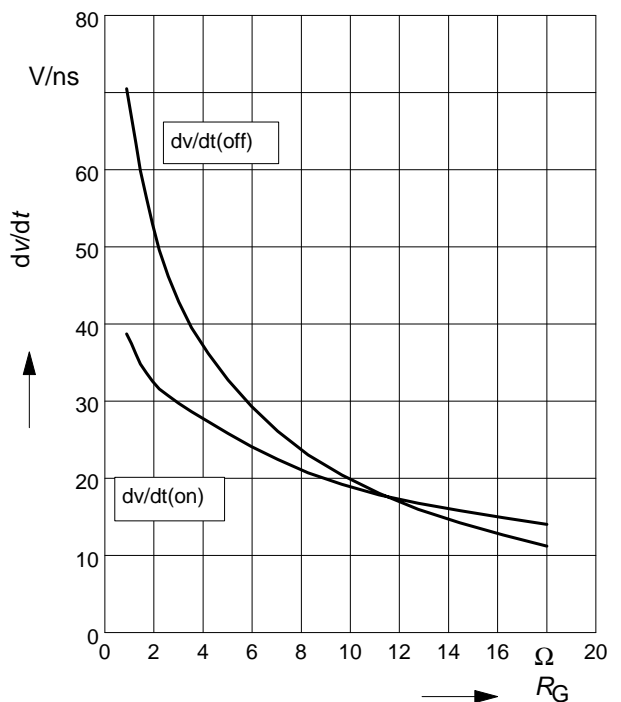
15 Typ. drain current slope

$di/dt = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $I_D = 47\text{A}$



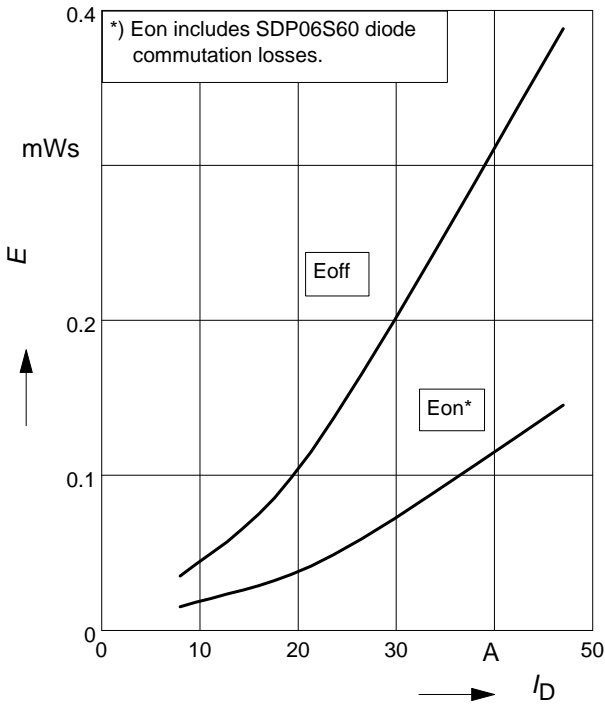
16 Typ. drain source voltage slope

$dv/dt = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$
 par.: $V_{DS} = 380\text{V}$, $V_{GS} = 0/+13\text{V}$, $I_D = 47\text{A}$



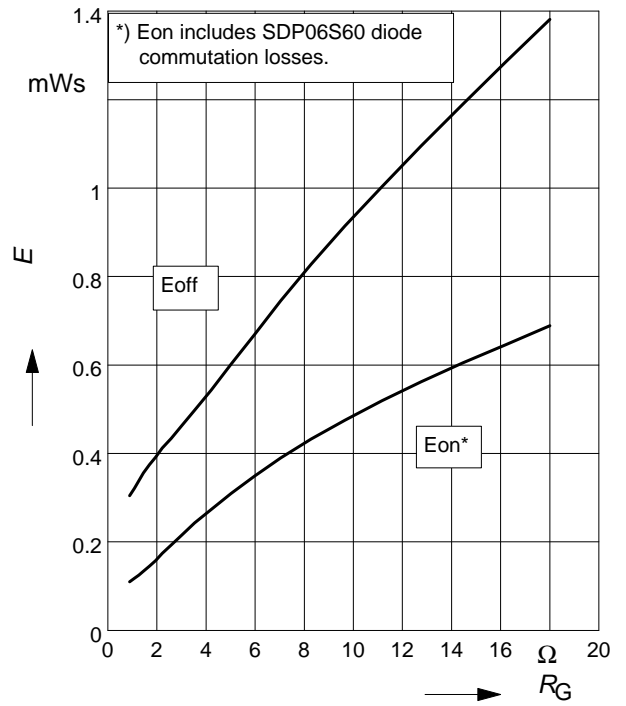
17 Typ. switching losses

$E = f(I_D)$, inductive load, $T_j=125^\circ\text{C}$
 par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $R_G=1.8\Omega$



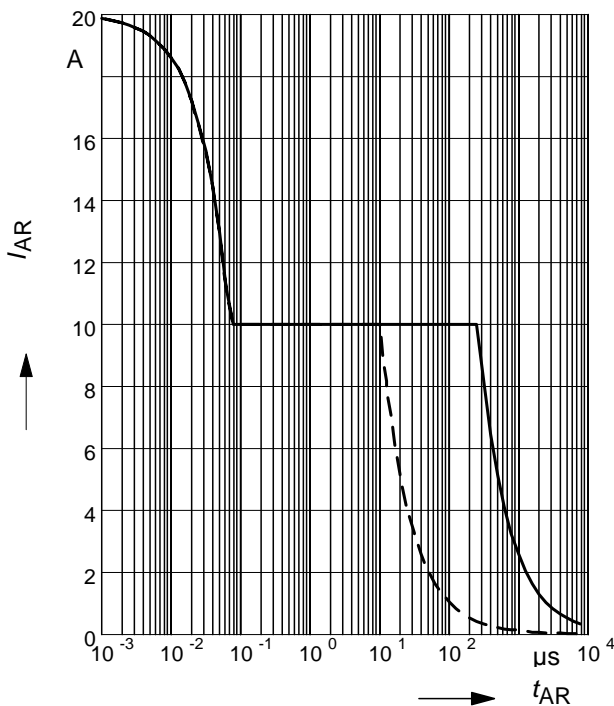
18 Typ. switching losses

$E = f(R_G)$, inductive load, $T_j=125^\circ\text{C}$
 par.: $V_{DS}=380\text{V}$, $V_{GS}=0/+13\text{V}$, $I_D=47\text{A}$



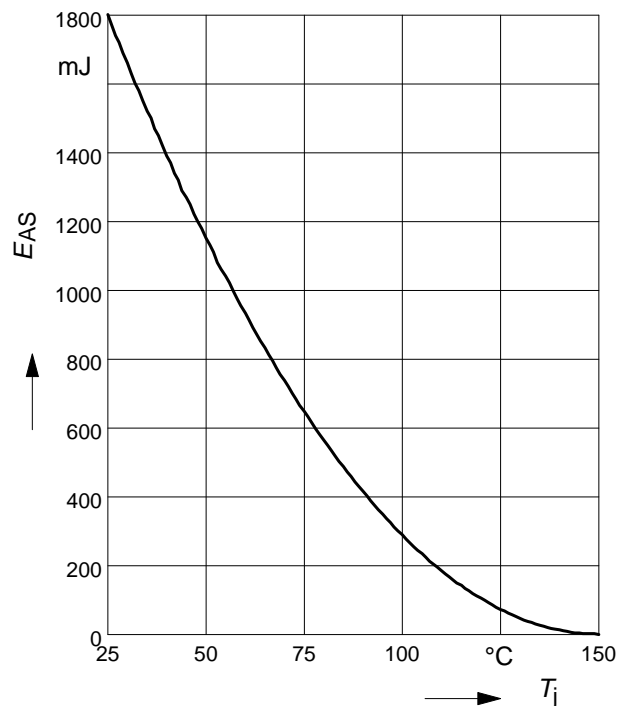
19 Avalanche SOA

$I_{AR} = f(t_{AR})$
 par.: $T_j \leq 150^\circ\text{C}$



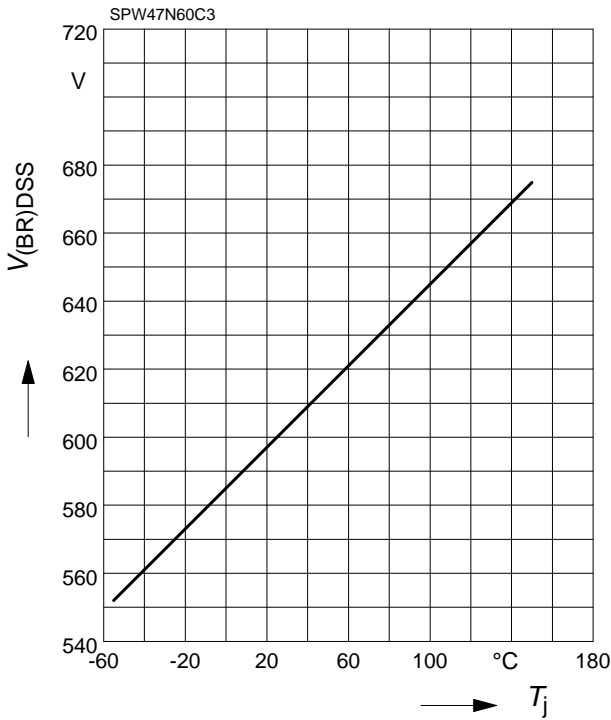
20 Avalanche energy

$E_{AS} = f(T_j)$
 par.: $I_D = 10\text{A}$, $V_{DD} = 50\text{V}$



21 Drain-source breakdown voltage

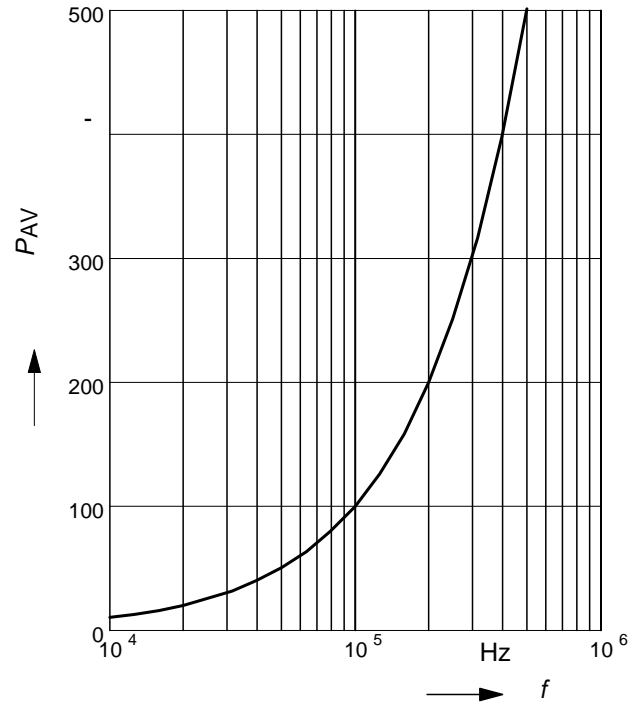
$$V_{(BR)DSS} = f(T_j)$$



22 Avalanche power losses

$$P_{AR} = f(f)$$

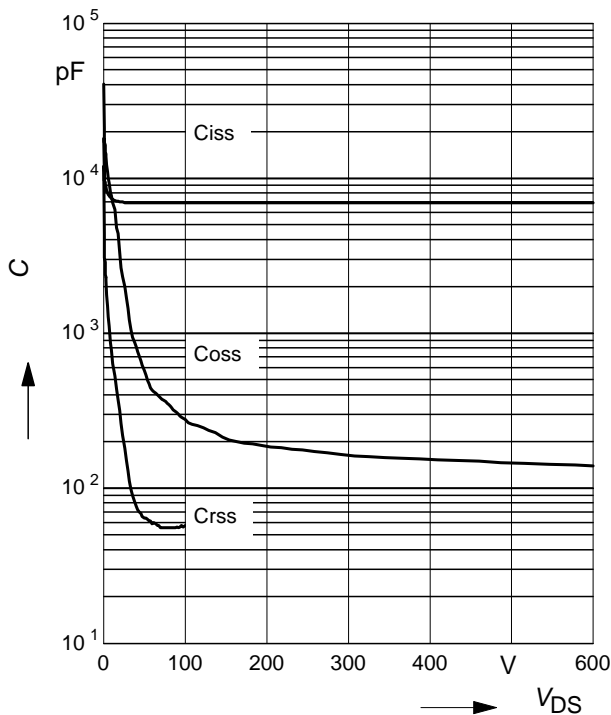
parameter: $E_{AR}=1mJ$



23 Typ. capacitances

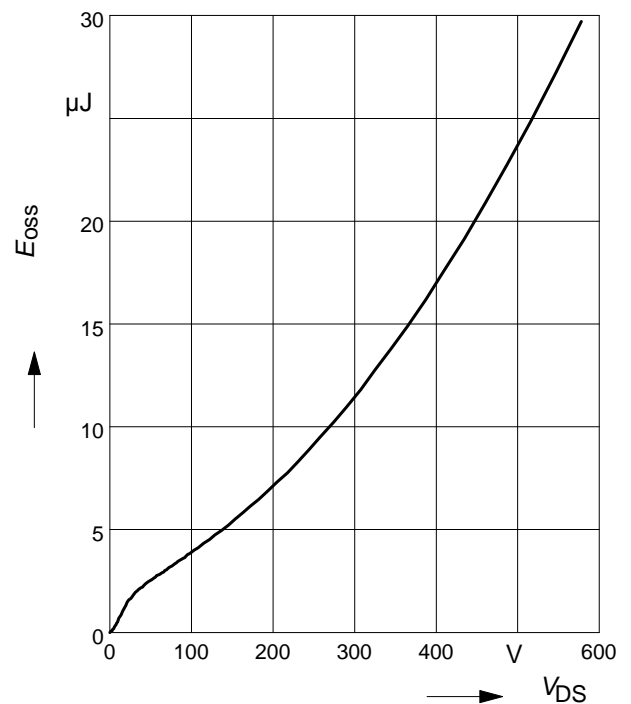
$$C = f(V_{DS})$$

parameter: $V_{GS}=0V, f=1 MHz$

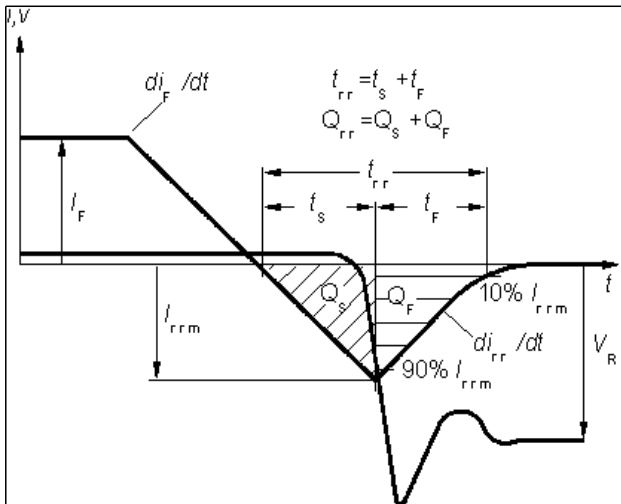


24 Typ. C_{OSS} stored energy

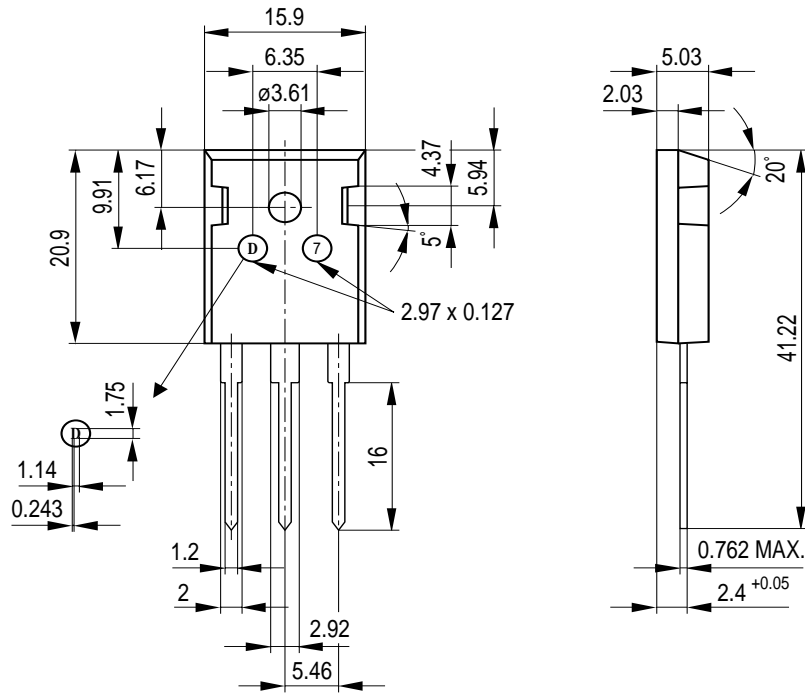
$$E_{OSS}=f(V_{DS})$$



Definition of diodes switching characteristics



P-TO-247-3-1



General tolerance unless otherwise specified: Leadframe parts: ± 0.05
 Package parts: ± 0.12

Published by
Infineon Technologies AG,
Bereichs Kommunikation
St.-Martin-Strasse 53,
D-81541 München
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